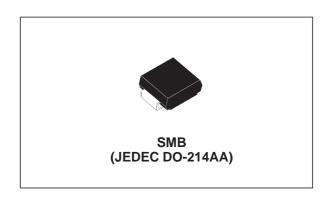


SMTPAxxx

TELECOM EQUIPMENT PROTECTION: TRISIL™

FEATURES

- Bidirectional crowbar protection
- Voltage range from 62V to 270V
- Low capacitance from 15pF to 30pF typ.@ 50V
- Low leakage current: I_R = 2µA max.
- Holding current: I_H = 150 mA Min.
- Repetitive peak pulse current: I_{PP} = 50 A (10/1000 μs)



MAIN APPLICATIONS

Telecommunication equipment such as:

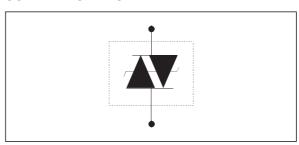
- Analog and digital line cards (xDSL, T1/E1, ISDN...).
- Terminals (phone, fax, modem...) and central office equipment.

DESCRIPTION

The SMTPAxxx series has been designed to protect telecommunication equipment against lightning and transient induced by AC power lines.

The package / die size ratio has been optimized by using the SMB package.

SCHEMATIC DIAGRAM



BENEFITS

Trisils are not subject to ageing and provide a fail safe mode in short circuit for a better protection. Trisils are used to help equipment to meet various standards such as UL1950, IEC950 / CSA C22.2, UL1459 and FCC part 68. Trisils have UL94 V0 resin approved. SMB package is JEDEC registred. (Trisils are UL 497B approved - file: E136224).

November 2002 - Ed: 4B 1/8

SMTPAxxx

IN COMPLIANCES WITH THE FOLLOWING STANDARDS

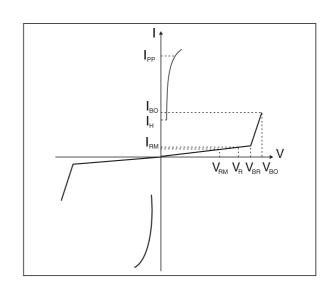
Standard	Peak Surge Voltage (V)	Voltage Waveform (µs)	Required peak current (A)	Current Waveform (µs)	Minimum serial resistor to meet standard (Ω)
GR-1089 Core First level	2500 1000	2/10 10/1000	500 100	2/10 10/1000	12 10
GR-1089 Core Second level	5000	2/10	500	2/10	24
GR-1089 Core Intra-building	1500	2/10	100 2/10		0
ITU-T-K20 / K21	6000 1500	10/700	150 37.5 5/310		53 0
ITU-T-K20 (IEC61000-4-2)	6000 8000	1/60 ns	ESD contact discharge ESD air discharge		0
VDE0433	4000 2000	10/700	100 50 5/310		21.5 0
VDE0878	4000 2000	1.2/50	100 50 1/20		0 0
IEC61000-4-5	4000 4000	10/700 1.2/50	100 100	5/310 8/20	21.5 0
FCC Part 68, lightning surge type A	1500 800	10/160 10/560	200 100	10/160 10/560	12.5 6.5
FCC Part 68, lightning surge type B	1000	9/720	25	5/320	0

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th} (j-a)	Junction to ambient with recommended footprint	100	°C/W
R _{th} (j-l)	Junction to leads	20	°C/W

$\begin{array}{l} \textbf{ELECTRICAL CHARACTERISTICS} \\ (T_{amb} = 25 ^{\circ} C) \end{array}$

Symbol	Parameter		
V _{RM}	Stand-off voltage		
I _{RM}	Leakage current at V _{RM}		
V _R	Continuous reverse voltage		
V _{BR}	Breakdown voltage		
V _{BO}	Breakover voltage		
IH	Holding current		
I _{BO}	Breakover current		
I _{PP}	Peak pulse current		
С	Capacitance		



ABSOLUTE RATINGS (T_{amb} = 25°C)

Symbol	Parameter	Value	Unit	
Ірр	Repetitive peak pulse current:	10/1000 µs 8/20 µs 10/560 µs 5/310 µs 10/160 µs 1/20 µs 2/10 µs	50 100 55 65 75 100 150	А
I _{FS}	Fail safe mode: maximum current	8/20 µs	2.5	kA
Ітѕм	Non repetitive surge peak on-state current (Sinusoidal)	t = 20ms t = 16.6ms t = 0.2s t = 2s	30 32 17 9	А
l²t	I²t value for fusing	t = 16.6ms t = 20ms	8.5 9	A²s
TL	Maximum lead temperature for soldering during 10	260	°C	
T _{stg} T _j	Storage temperature range Maximum junction temperature		- 55 to + 150 150	°C

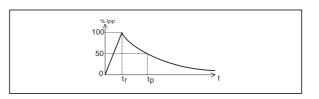
Repetitive peak pulse current

tr: rise time (µs)

tp: pulse duration time (µs)

ex.: Pulse waveform 10/1000µs

 $tr = 10 \mu s$ $tp = 1000 \mu s$



ELECTRICAL PARAMETERS (Tamb = 25°C)

Туре	I _{RM} @ V _{RM} max		I _R @ V _R MAX		DYNAMIC V _{BO} @ I _{BO} max Note 2		STATIC V _{BO} @ I _{BO} max Note 3		I _H min Note 4	C typ.	c typ.
	μA	V	μA	V	V	mA	v	mA	mA	pF	pF
SMTPA62		56		62	85		82		150	30	50
SMTPA68		61		68	93		90		150	30	45
SMTPA100		90		100	135		133		150	20	40
SMTPA120		108		120	160		160		150	20	40
SMTPA130	_	117	50	130	173	000	173	000	150	20	35
SMTPA180	2	162	50	180	235	800	240	800	150	15	30
SMTPA200		180		200	262		267		150	15	30
SMTPA220		198		220	285		293		150	15	30
SMTPA240		216		240	300		320		150	15	30
SMTPA270		243		270	350		360		150	15	30

Note 1: I_R measured at V_R guarantee $V_{BRmin} \ge V_R$ Note 2: See functional breakover voltage test circuit 1.

Note 3: See test circuit 2.

Note 4: See functional holding current test circuit 3. Note 5: $V_R = 50V$ bias, VRMS = 1V, F = 1MHz. Note 6: $V_R = 2V$ bias, VRMS = 1V, F = 1MHz

Fig. 1: Non repetitive surge peak on-state current versus overload duration (Tj initial = 25°C)

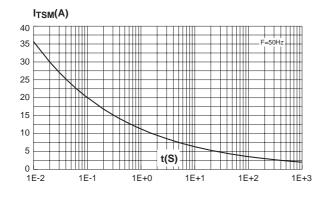


Fig. 2: On-state voltage versus on-state current (typical values).

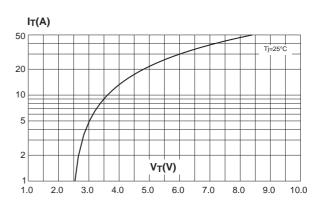


Fig. 3: Relative variation of holding current versus junction temperature.

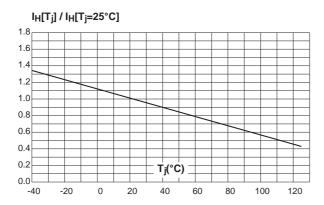


Fig. 5: Relative variation of leakage current versus

junction temperature (typical values).

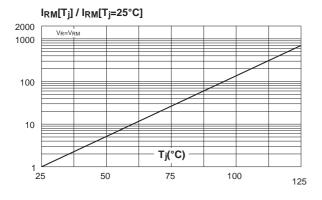


Fig. 7: Relative variation of junction capacitance versus reverse voltage applied (typical values).

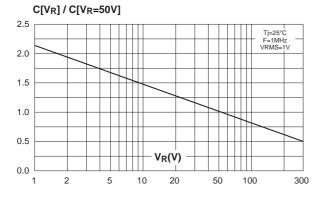


Fig. 4: Relative variation of breakover voltage versus junction temperature.

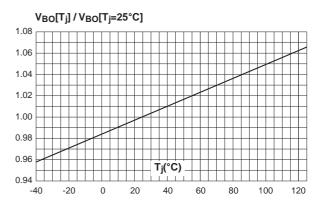
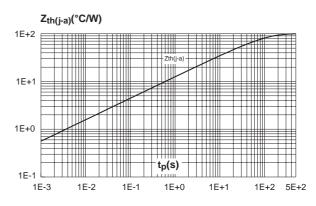
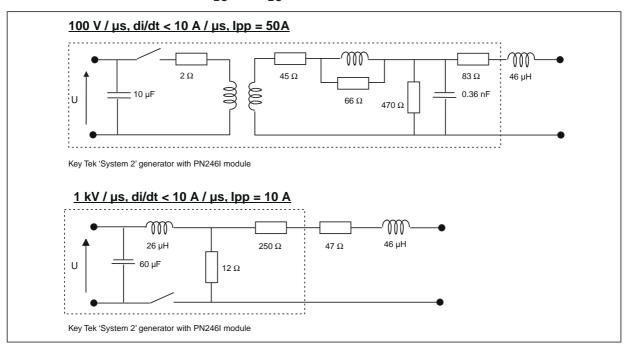


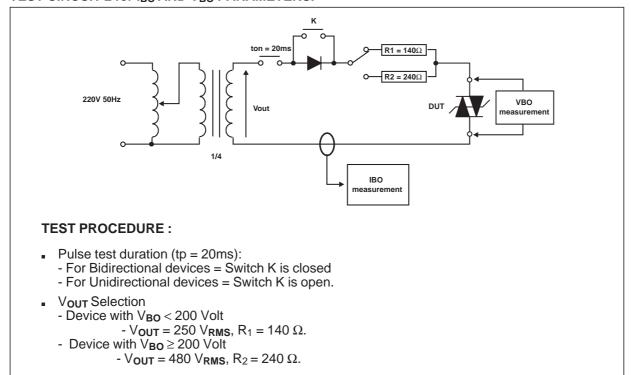
Fig. 6: Relative variation of thermal impedance versus pulse duration.



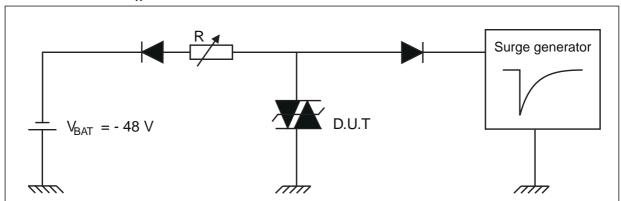
TEST CIRCUIT 1 FOR DYNAMIC IBO and VBO PARAMETERS



TEST CIRCUIT 2 for IBO AND VBO PARAMETERS.



TEST CIRCUIT 3 for I_H PARAMETERS.



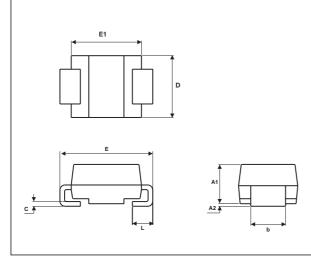
This is a GO-NO GO test which allows to confirm the holding current (I_H) level in a functional test circuit.

TEST PROCEDURE:

- Adjust the current level at the $I_{\mbox{\scriptsize H}}$ value by short circuiting the D.U.T.
- Fire the D.U.T. with a surge current : I_{pp} = 10A, 10/1000 $\mu s.$
- The D.U.T. will come back to the off-state within 50 ms max.

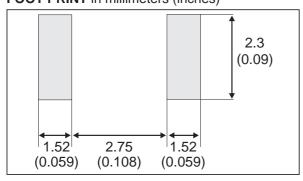
PACKAGE MECHANICAL DATA

SMB (JEDEC DO-214AA)



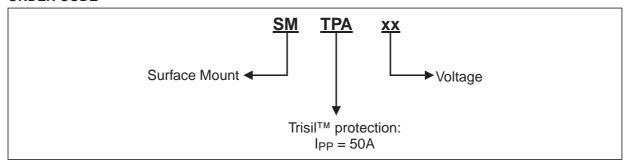
	DIMENSIONS					
REF.	Millimeters		Inc	hes		
	Min.	Max.	Min.	Max.		
A1	1.90	2.45	0.075	0.096		
A2	0.05	0.20	0.002	0.008		
b	1.95	2.20	0.077	0.087		
С	0.15	0.41	0.006	0.016		
E	5.10	5.60	0.201	0.220		
E1	4.05	4.60	0.159	0.181		
D	3.30	3.95	0.130	0.156		
Ĺ	0.75	1.60	0.030	0.063		

FOOT PRINT in millimeters (inches)



577

ORDER CODE



ORDERING INFORMATION

Part number	Marking	Package	Weight	Base qty	Delivery mode
SMTPA62	U01				
SMTPA68	U05		0.11 g	5000	Tape & reel
SMTPA100	U13				
SMTPA120	U17	SMB			
SMTPA130	U19				
SMTPA180	U25				
SMTPA200	U27				
SMTPA220	U31				
SMTPA240	U35				
SMTPA270	U39				

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied.

change without notice. This publication supersedes and replaces all information previously supplied.

STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 2002 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore

Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com

57